Effects of heat-treatment of silica and precursor on the surface density of aminosilanes deposited onto silica by ALD Satu Ek, Eero I. Iiskola, Lauri Niinistö Laboratory of Inorganic and Analytical Chemistry, Helsinki University of Technology, P.O.Box 6100, FIN-02015 Espoo, Finland

Amino-terminated molecular layers on silicon dioxide surfaces are widely used as coupling agents. Amino-functionalized surfaces are frequently utilized in chromatography, catalyst technology, biochemistry and electronics, for example (1). Amino-terminated layers can be obtained by binding aminopropylalkoxysilanes onto the solid surface. The preparation of aminosilanemodified surfaces is most often carried out in the liquid phase. Nevertheless, the surface-controlled gas-phase deposition, ALD (atomic layer deposition) (2), eliminates many of the tedious operations of the liquid-phase technique, such as controlled hydrolysis of alkoxysilanes, solvent removal and recovery, washing procedures and other manipulations (3). In addition, a very reproducible product can be achieved by ALD.

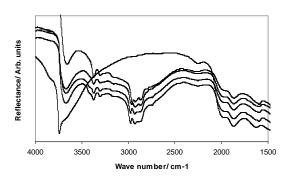
In this work, we have studied the gas-phase modification of porous silica with four precursors: yaminopropyltrimethoxysilane (APTMS), γaminopropyltriethoxysilane (APTS), yaminopropyldiethoxymethylsilane (APDMS) and yaminopropyldimethylethoxysilane (APDMES). Surfacesaturated layers of aminosilanes were deposited on silica at a low reaction temperature, i.e. 150 °C, and at a pressure of 20-50 mbar. When aminosilanes are attached onto the silica surface a sharp peak due to stretching vibration of free OH groups at 3748-3740 cm<sup>-1</sup> disappears in the DRIFT spectrum (Fig. 1). At the same time bands corresponding to IR -vibrations for N-H and C-H bonds appear in the spectra. In addition, a broad band for unreacted silanol groups hydrogen-bonded to alkoxy groups is seen in the DRIFT spectra at 3740-3500 cm<sup>-1</sup>. At high pretreatment temperatures of silica strained siloxane bridges are assumed to be opened and reacted with aminosilanes.

The effect of heat-treatment temperature of silica on the achieved surface density of aminosilanes was studied on silica pretreated at 200-800 °C on the basis of elemental analyses. The pretreatment temperature of silica was observed to have a distinct influence on the surface density of aminosilanes (Fig. 2, Tables 1 and 2). The surface densities decreased from 1.8-2.1 amino groups/nm<sup>2</sup> to 1.1-1.4 amino groups/nm<sup>2</sup> when the pretreatment temperature of silica was increased. The most dense moelcular layer was achieved with APDMS on silica heat-treated at 200 °C. However, the differences between the precursors were not large considering the surface densities achieved.

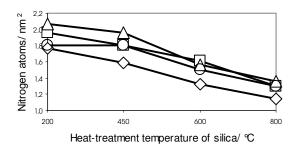
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**Fig. 1.** DRIFT spectra of silica heat-treated at 450 °C and APTMS, APTS, APDMS, APDMES –modified silica (from below upwards).



**Fig. 2.** Effect of heat-treatment and precursor on the surface density of aminosilanes;  $\Diamond = APTMS \square = APTS \triangle = APDMS \bigcirc APDMES$ .

 Table 1. Results of elemental analyses for aminosilane 

 modified silica.

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	APTMS		APTS				
Heat-	Ν	С	Ν	С			
treatment	atoms/	atoms/	atoms/	atoms/			
of silica	$nm^2$	$nm^2$	$nm^2$	$nm^2$			
/ °C							
200	1.8	7.5	2.0	7.3			
450	1.6	7.3	1.8	6.9			
600	1.3	7.1	1.6	7.3			
800	1.1	5.9	1.3	5.3			

 Table 2. Results of elemental analyses for aminosilane

modified silica.							
	APDMS		APDMES				
Heat-	Ν	С	Ν	С			
treatment	atoms/	atoms/	atoms/	atoms/			
of silica	$nm^2$	$nm^2$	$nm^2$	$nm^2$			
/ °C							
200	2.1	7.9	1.8	7.8			
450	2.0	6.8	1.8	8.2			
600	1.6	6.9	1.5	7.4			
800	1.4	6.5	$1.3^{*}$	$6.3^{*}$			

\* heat-treatment of silica was performed at 820 °C instead of 800 °C.